NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI UML1T** is Designed for

FEATURES:

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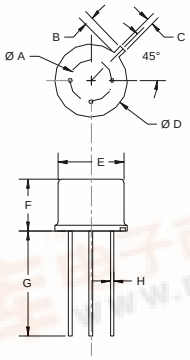
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	0.4 A
V_{CBO}	55 V
V_{CEO}	30 V
V_{EBO}	3.5 V
P_{DISS}	5.0 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	35.0 °C/W

PACKAGE STYLE TO-39



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.200 / 5.080	
B	.029 / 0.740	.045 / 1.140
C	.028 / 0.720	.034 / 0.860
D	.335 / 8.510	.370 / 9.370
E	.305 / 7.750	.335 / 8.500
F	.240 / 6.100	.260 / 6.600
G	.500 / 12.700	
H	.016 / 0.407	.020 / 0.508

ORDER CODE: ASI10690

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 5 mA			30			V
BV_{CER}	I_C = 5 mA	R_{BE} = 10 Ω		55			V
BV_{CBO}	I_C = 0.1 mA			55			V
BV_{EBO}	I_E = 0.1 mA			3.5			V
I_{CEO}	V_{CE} = 28 V					20	µA
I_{CEX}	V_C = 55 V	V_{BE} = -1.5 V				100	µA
h_{FE}	V_{CE} = 5.0 V	I_C = 50 mA I_C = 360 mA		10 5		200 ---	---
C_{OB}	V_{CB} = 28 V		f = 1.0 MHz			5.0	pF
P_{GE} η_D	V_{CC} = 28 V	P_{OUT} = 1.0 W	f = 400 MHz	10	55		dB %